

# P30W60HP2V

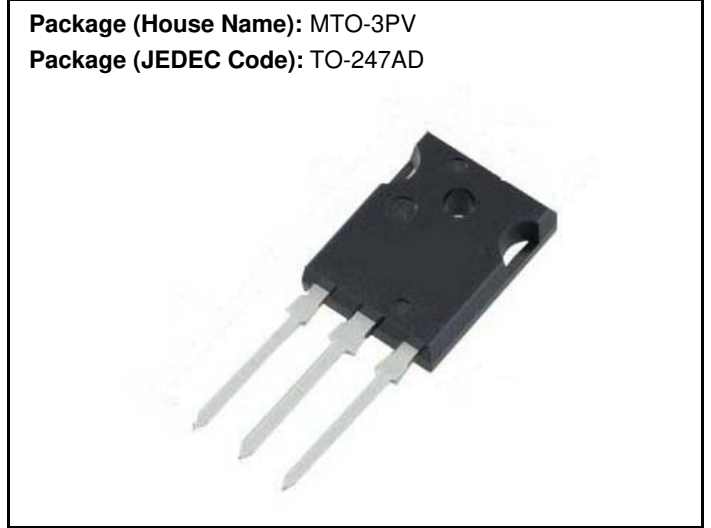
**Power MOSFETs**  
**600V, 30A, N-channel**

**Feature**

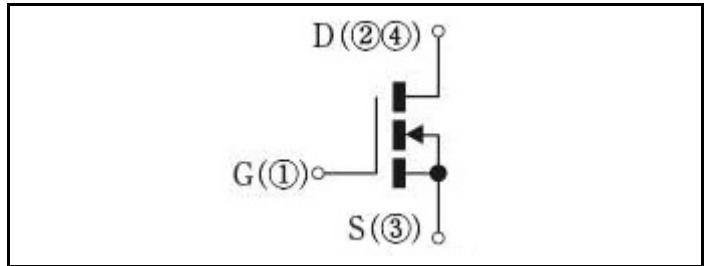
- N-channel
- High Voltage
- High Speed Switching
- Low Ron
- Low Capacitance
- High Avalanche Durability, High di/dt Durability
- Pb free terminal
- RoHS:Yes

**OUTLINE**

**Package (House Name):** MTO-3PV  
**Package (JEDEC Code):** TO-247AD



**Equivalent circuit**



**Absolute Maximum Ratings** (unless otherwise specified : Tc=25°C)

Item	Symbol	Conditions	Ratings	Unit
Storage temperature	Tstg		-55 to 150	°C
Channel temperature	Tch		-55 to 150	°C
Drain-source voltage	V <sub>DSS</sub>		600	V
Gate-source voltage	V <sub>GSS</sub>		±30	V
Continuous drain current(DC)	I <sub>D</sub>		30	A
Continuous drain current(Peak)	I <sub>DP</sub>	Pulse width 10µs, duty=1/100	120	A
Continuous source current(DC)	I <sub>S</sub>		30	A
Total power dissipation	P <sub>T</sub>		310	W
Repetitive avalanche current	I <sub>AR</sub>	Starting Tch=25°C Tch≤150°C	30	A
Single avalanche energy	E <sub>AS</sub>	Starting Tch=25°C Tch≤150°C	160	mJ
Repetitive avalanche energy	E <sub>AR</sub>	Starting Tch=25°C Tch≤150°C	16	mJ
Drain-source diode di/dt strength	di/dt	I <sub>S</sub> =30A, Tc=25°C	350	A/µs
Mounting torque	TOR	(Recommended torque : 0.5N·m)	0.8	N·m

\* : See the original Specifications

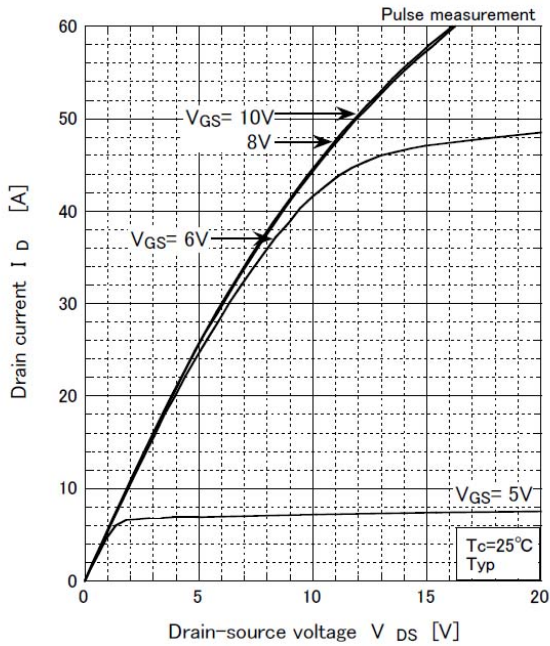
**Electrical Characteristics** (unless otherwise specified : Tc=25°C)

Item	Symbol	Conditions	Ratings			Unit
			MIN	TYP	MAX	
Drain-Source breakdown voltage	$V_{(BR)DSS}$	ID=1mA, VGS=0V	600			V
Zero gate voltage drain current	$I_{DSS}$	VDS=600V, VGS=0V			100	μA
Gate-source leakage current	$I_{GSS}$	VGS=±30V, VDS=0V			±0.1	μA
Forward transconductance	$g_{fs}$	ID=15A, VDS=10V	16.5	33		S
Static drain-source on-state resistance	$R_{DS(ON)}$	ID=15A, VGS=10V		0.185	0.23	Ω
Gate threshold voltage	$V_{th}$	ID=3mA, VDS=10V	3	3.75	4.5	V
Source-drain diode forward voltage	$V_{SD}$	IS=15A, VGS=0V			1.5	V
Thermal resistance	$R_{th(j-c)}$	Junction to case, with heatsink			0.4	°C/W
Total gate charge	$Q_g$	VDD=400V, VGS=10V, ID=30A		70		nC
Input capacitance	$C_{iss}$	VDS=50V, VGS=0V, f=1MHz		3935		pF
Reverse transfer capacitance	$C_{rss}$	VDS=50V, VGS=0V, f=1MHz		6.8		pF
Output capacitance	$C_{oss}$	VDS=50V, VGS=0V, f=1MHz		305		pF
Turn-on delay time	$t_{d(on)}$	ID=15A, RL=10Ω, VDD=150V, Rg=50Ω, VGS(+)=10V, VGS(-)=0V		71		ns
Rise time	$t_r$	ID=15A, RL=10Ω, VDD=150V, Rg=50Ω, VGS(+)=10V, VGS(-)=0V		78		ns
Turn-off delay time	$t_{d(off)}$	ID=15A, RL=10Ω, VDD=150V, Rg=50Ω, VGS(+)=10V, VGS(-)=0V		256		ns
Fall time	$t_f$	ID=15A, RL=10Ω, VDD=150V, Rg=50Ω, VGS(+)=10V, VGS(-)=0V		65		ns

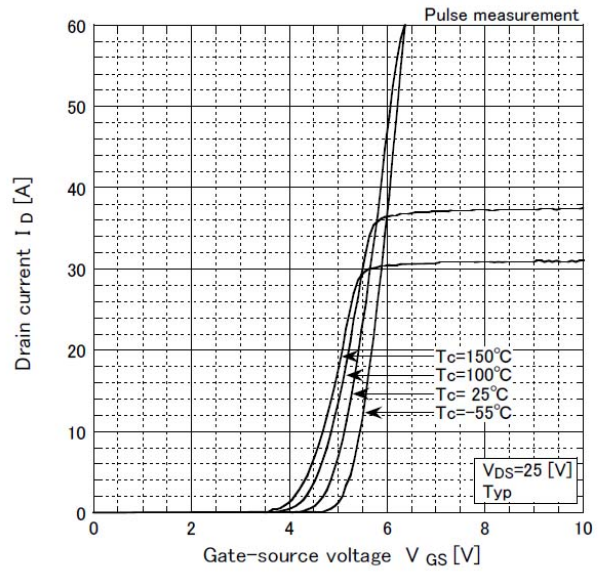
\* : See the original Specifications

# CHARACTERISTIC DIAGRAMS

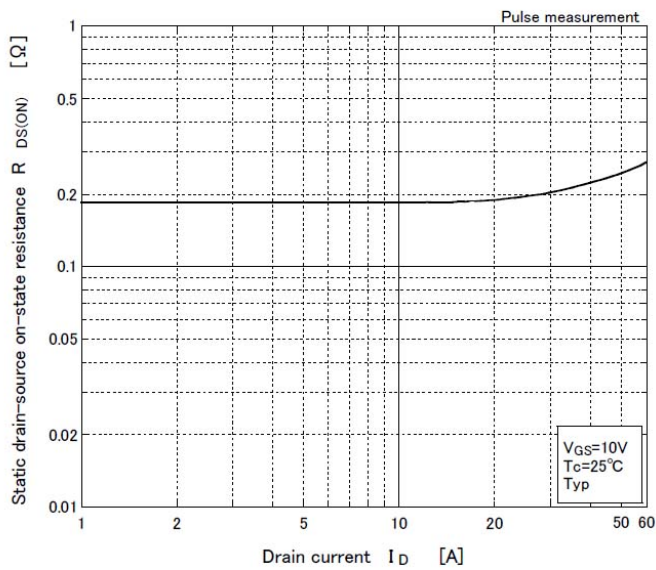
Typical output characteristics



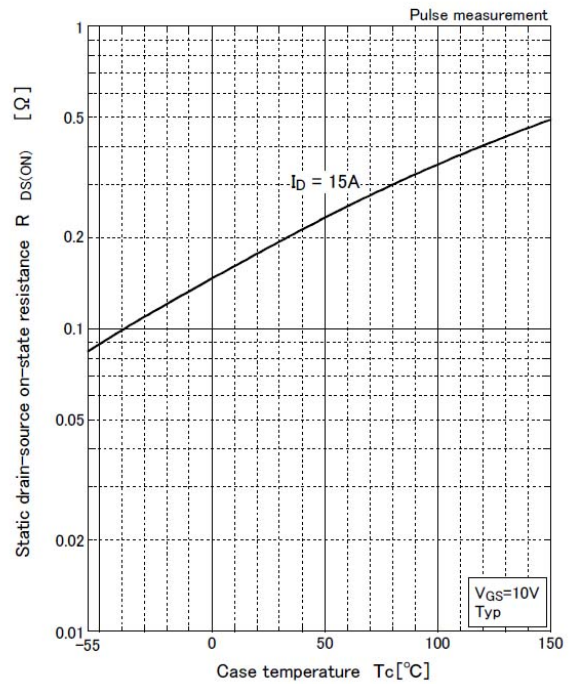
Transfer characteristics

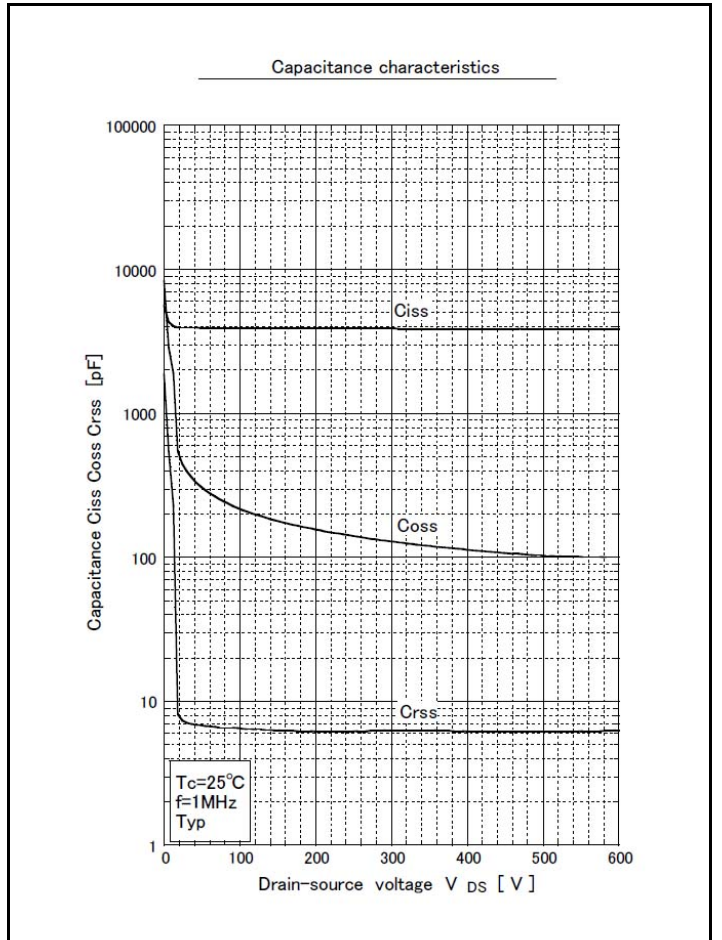
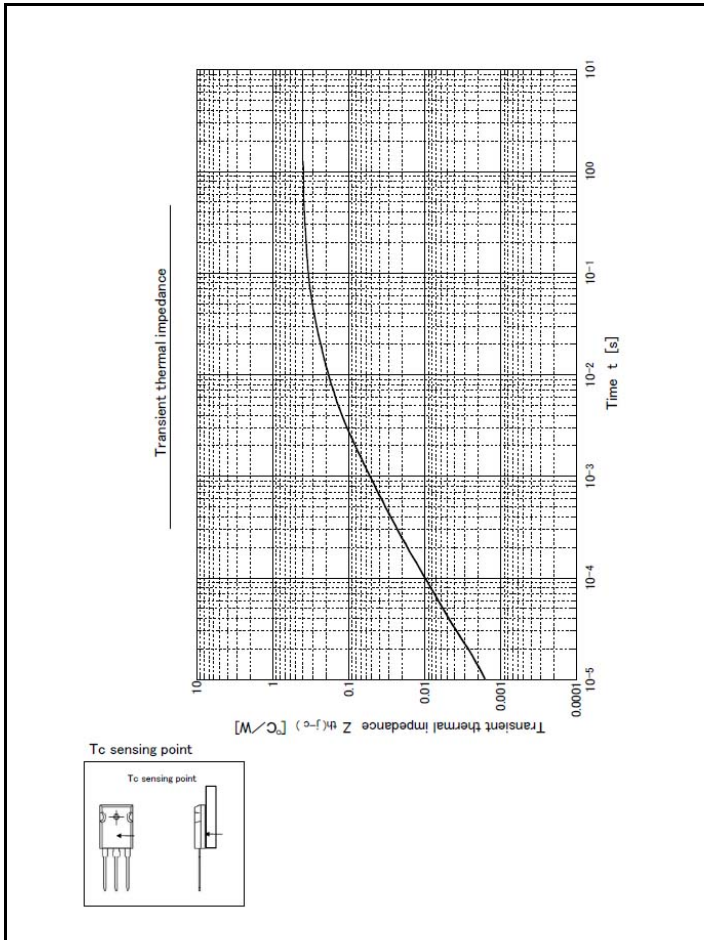
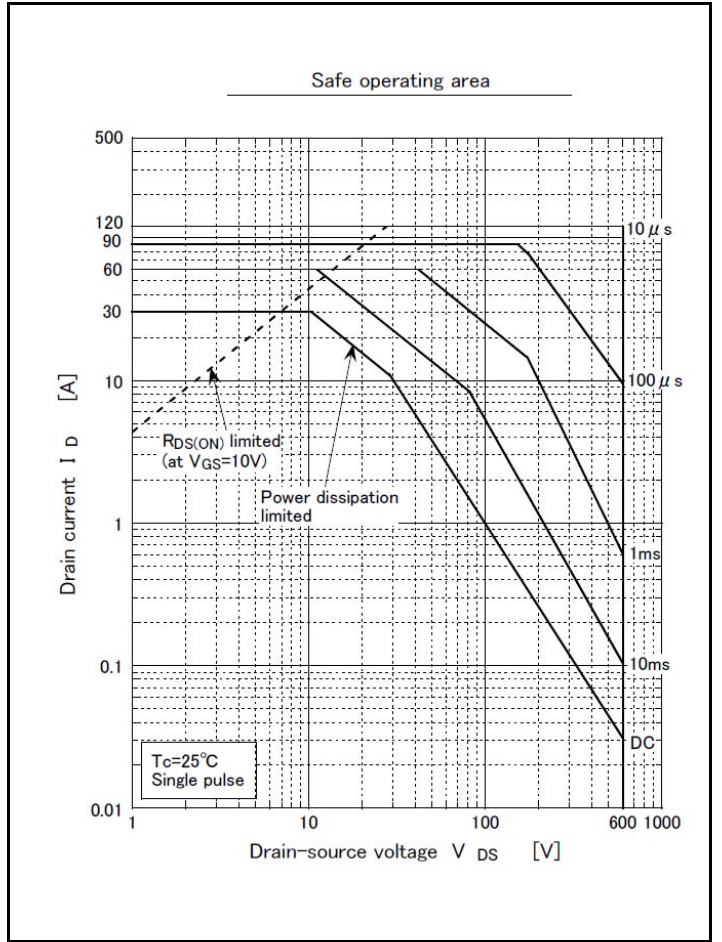
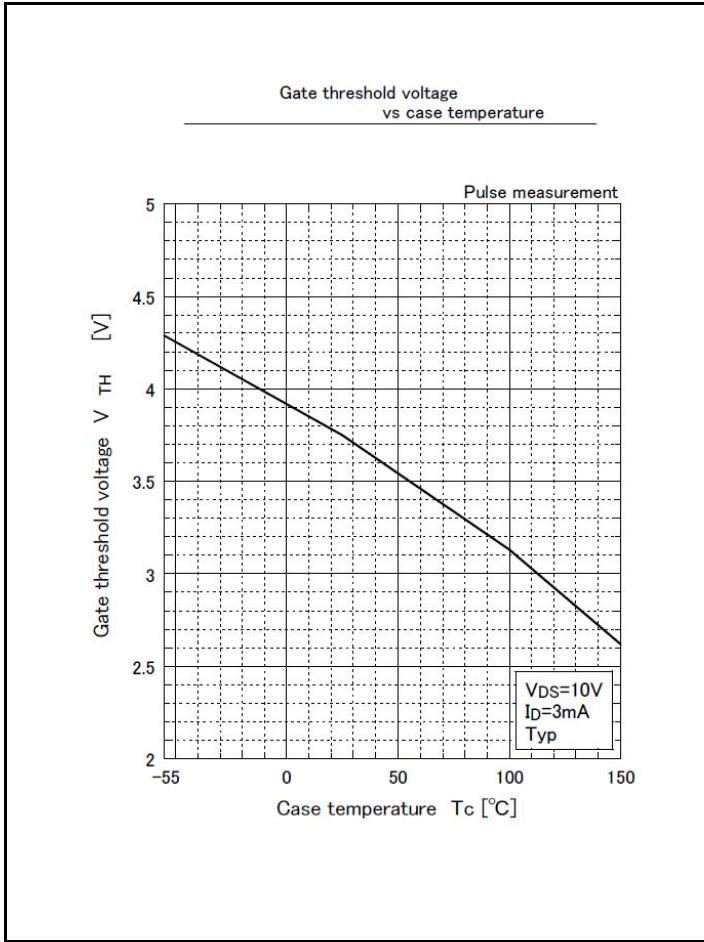


Static drain-source on-state resistance vs drain current

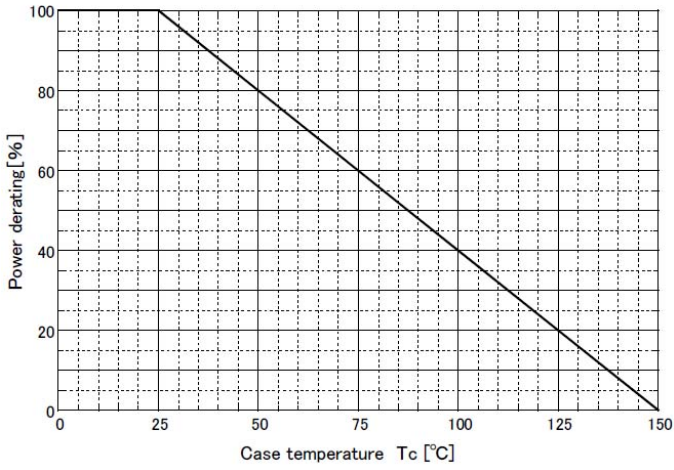


Static drain-source on-state resistance vs case temperature

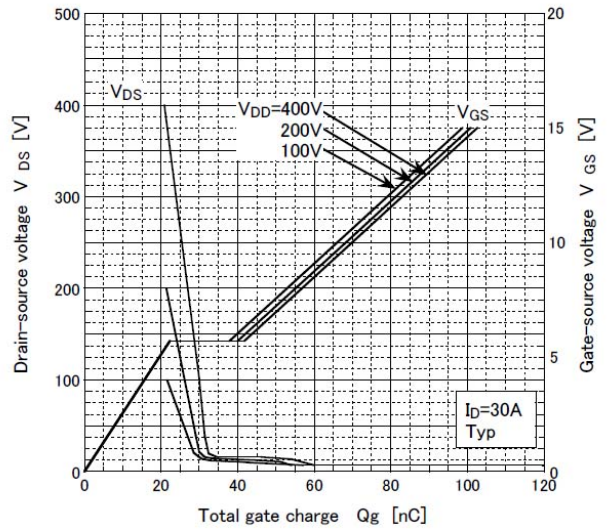




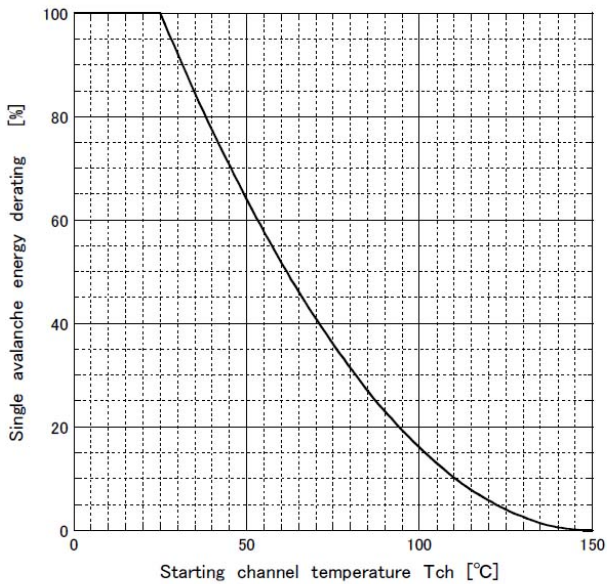
Power derating - case temperature



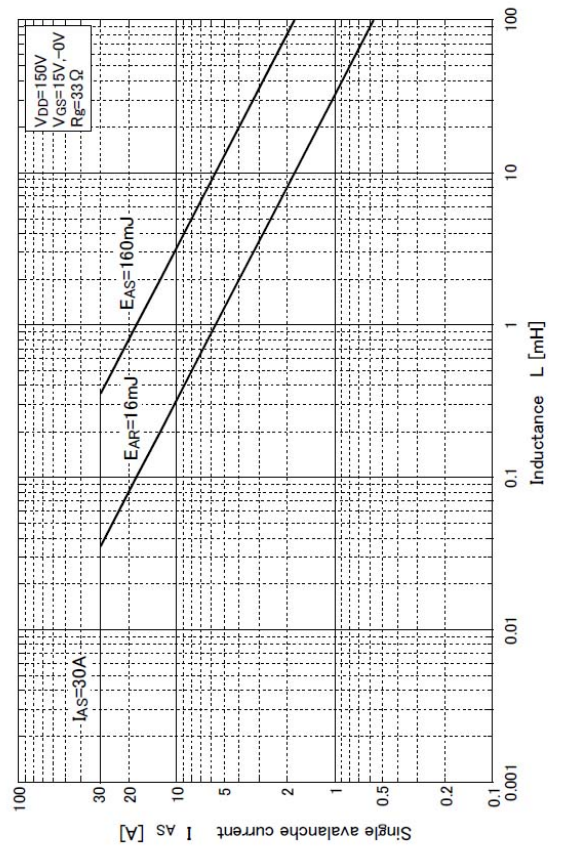
Gate charge characteristics



Single avalanche energy derating vs channel temperature

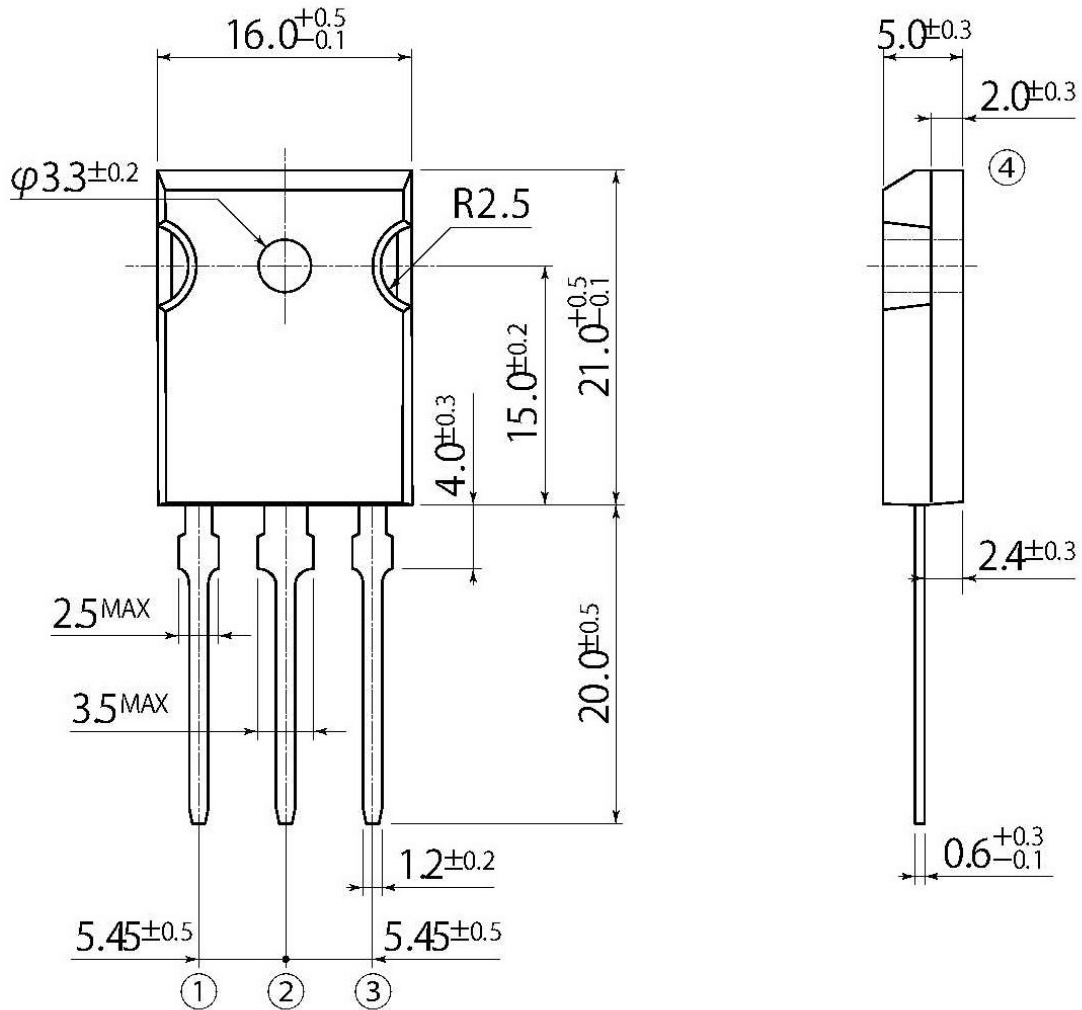


Single avalanche current vs inductive load



K7

JEDEC Code	TO-247AD
JEITA Code	-
House Name	MTO-3PV



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